ELE 455/555 Computer System Engineering

Section 3 – Memory Class 1 – Memory Overview

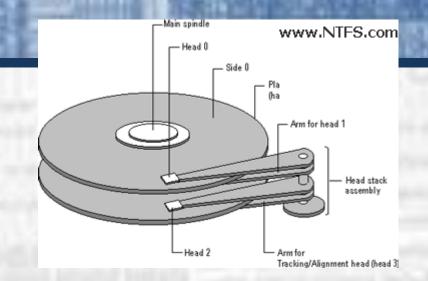
- Current memory systems
 - Magnetic Disk
 - Flash
 - DRAM
 - SRAM

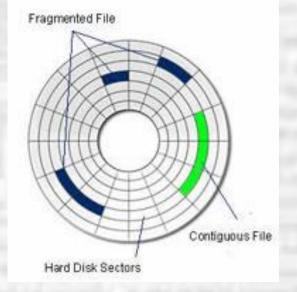
- Magnetic Disk
 - Platter
 - Ferro-magnetic coating on a circular platter
 - Magneto-resistive
 - Giant Magneto-resistive
 - Tunneling Magneto-resistive
 - 2 sided
 - Magnetized by applying a magnetic field
 - Read by passing a coil over the magnetized area

- Magnetic Disk
 - Platter
 - Platter spins at a constant rate
 - read/write heads are semi-fixed
 - Platter is broken into annular "tracks"
 - Tracks are broken into contiguous "sectors"
 - Bits are read and written in 512K Byte sectors
 - Bit density (area) changes with respect to the distance from the center
 - Outside edge moving very quickly

- Magnetic Disk
 - "flying" head
 - Contains both a read and a write capability
 - Mechanically designed to:
 - Swing from outside edge to inside edge
 - Provides access to all tracks
 - Fly a few nm above the disk
 - Concept is called an "air bearing"

- Magnetic Disk
 - Hard Disk Drive
 - 2.6" to 3.7" platters
 - Mobile devices down to 0.75"
 - 1-5 platters / drive
 - 1000s of tracks / platter





- Magnetic Disk
 - Hard Disk Drive
 - Specifications
 - 2TByte data storage
 - 5400 rpm platter rotation
 - 12ms seek time time to randomly access a sector
 - 8MByte buffer
 - \$100
 - 50nCents / Kbyte

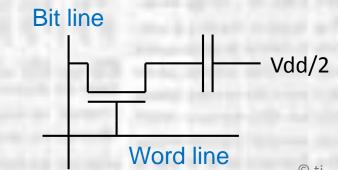
- Flash
 - Future addition
 - Not common in "computer" systems

• SDRAM

- Capacitor based storage
 - Requires refresh
- Dynamic
- Random Access
- Row and Column access architecture
- Synchronous
 - Clock (and outputs)matched to processor bus
- Burst mode

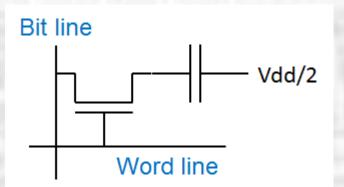
Allows additional bytes to be read on a single address access
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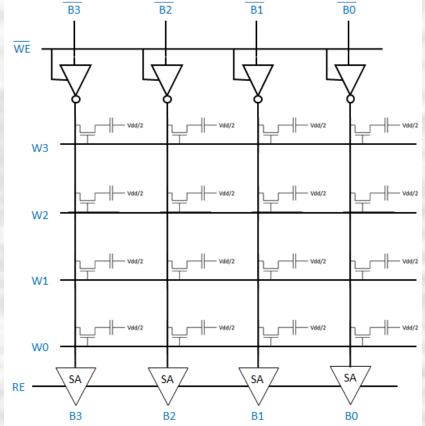
- SDRAM Synchronous Dynamic Random Access Memory
 - Memory cell (1 bit) is based on capacitor charge storage
 - Bit value decays over time
 - must be recharged called a refresh cycle
 - Standard SDRAM transfers 1 word each array access
 - DDR double data rate transfers 2 words each array access
 - DDR2, DDR3, DDR4 transfer 4,8,16 words each array access
 - Medium speed
 - Highest density
 - Used as main memory



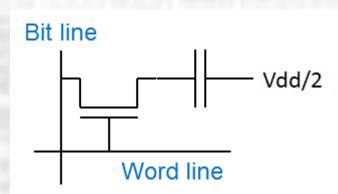
• SDRAM – Synchronous Dynamic Random Access Memory

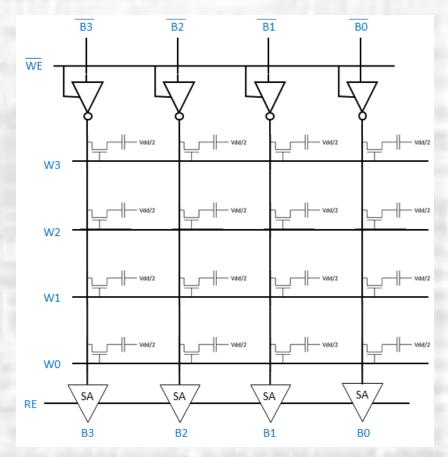
- Write
 - All Word lines low
 - Read Enable (RE) disabled (low)
 - Place B0, B1, B2, B3 on inputs
 - Pull write enable bar (WE) low
 - Strobe the desired word line high
 - Bit lines write to the bit cell capacitors



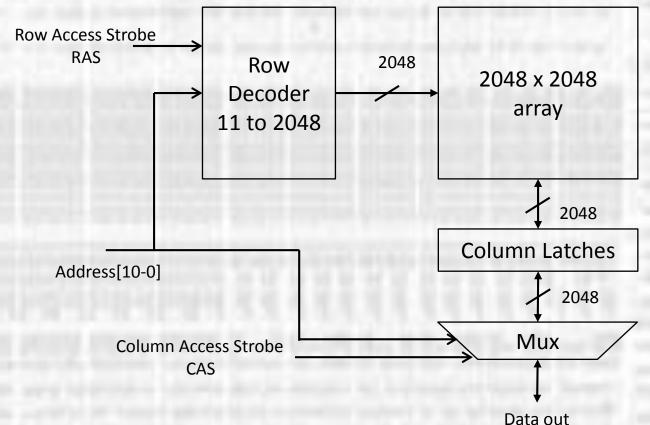


- SDRAM Synchronous Dynamic Random Access Memory
 - Read
 - All Word lines low
 - Write enable bar (WE) high
 - inverters tristated
 - Read Enable (RE) high
 - Strobe the desired word line high
 - Sense amplifiers read the value of the capacitors

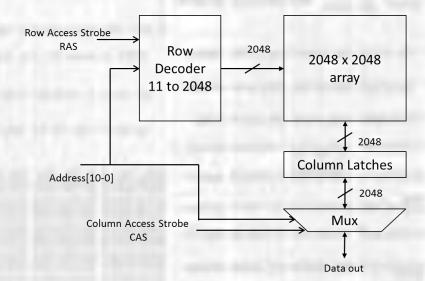




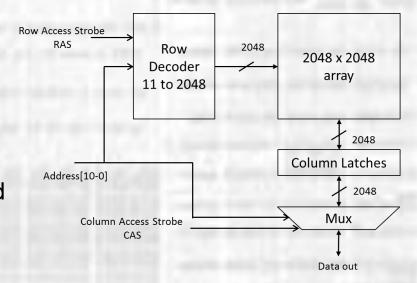
- SDRAM
 - Array Layout 4M X 1 DRAM



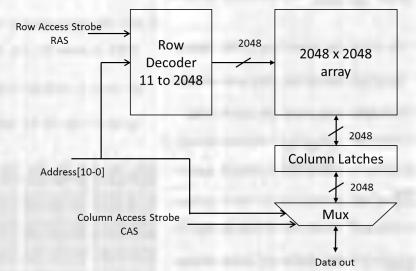
- SDRAM
 - Random Access
 - 4M bits → 22 address bits
 - Operation
 - Place upper 11 bits on address bus
 - Strobe RAS
 - 2048 bits are latched
 - Place lower 11 bits on address bus
 - Strobe CAS
 - Selected bit is fed out



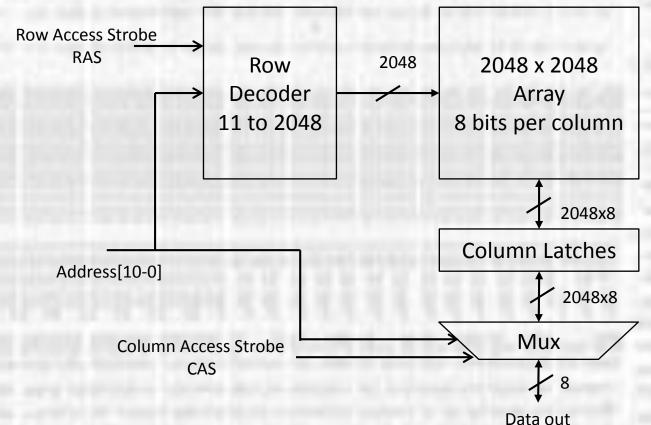
- SDRAM
 - Refresh
 - Operation
 - Controller selects a row address Read
 - 2048 bits are latched
 - Same row address Write
 - 2048 bits are refreshed

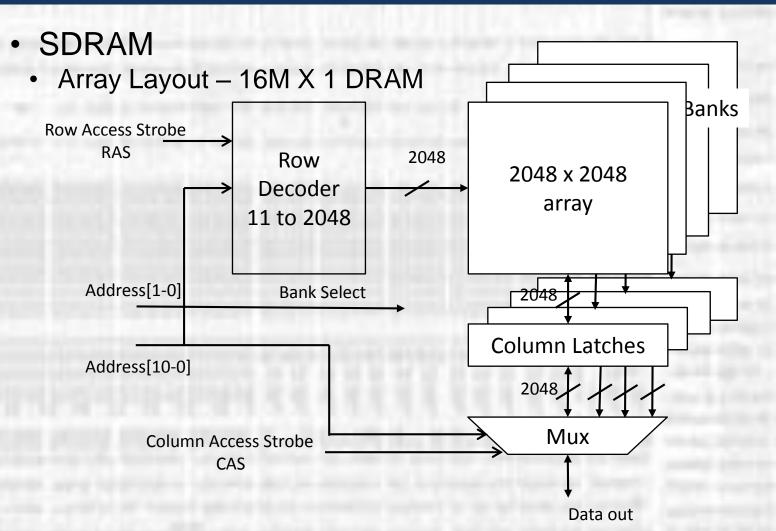


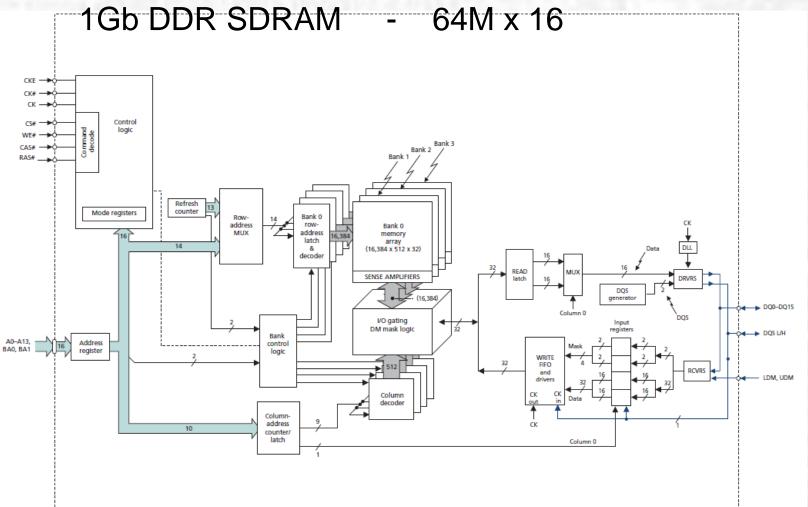
- SDRAM
 - Burst Operation
 - 4M bits → 22 address bits
 - Operation
 - Place upper 11 bits on address bus
 - Strobe RAS
 - 2048 bits are latched
 - Place lower 11 bits on address bus
 - Strobe CAS
 - Selected bit is fed out
 - Increment address latch
 - Next clock
 - Next bit is fed out



- SDRAM
 - Array Layout 4M X 8 DRAM

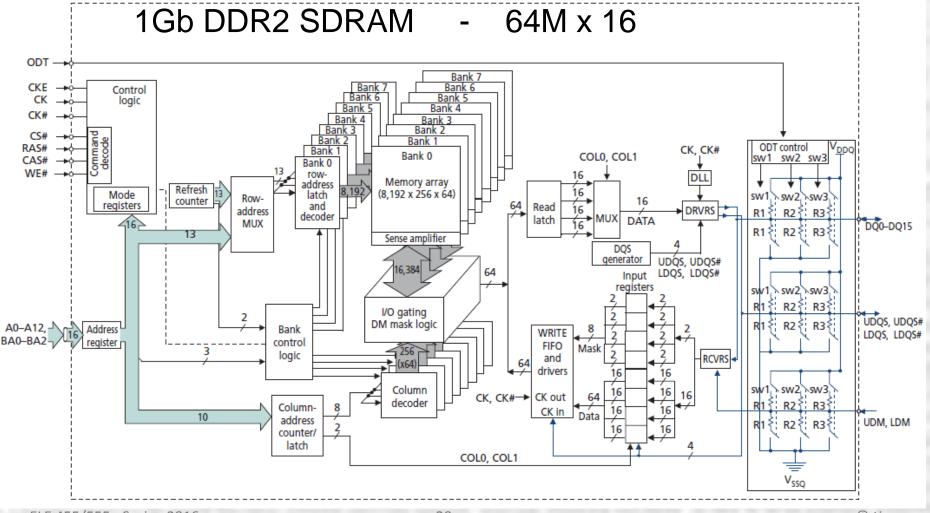






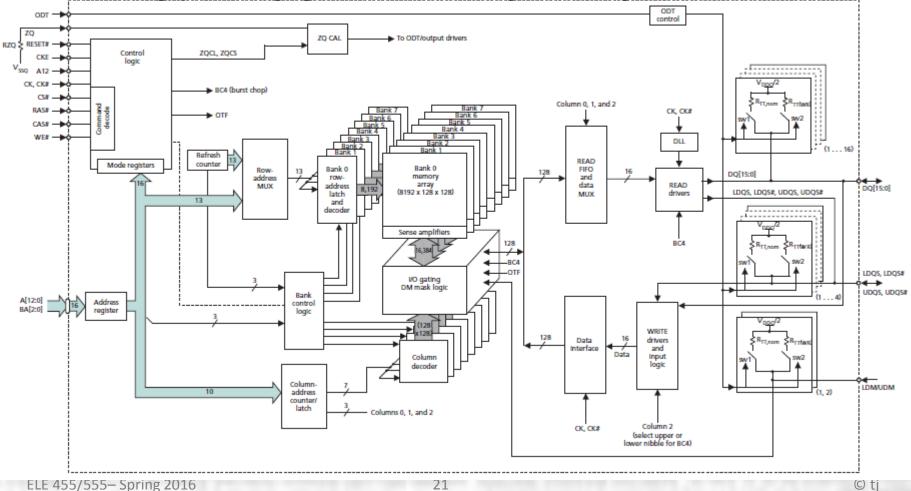
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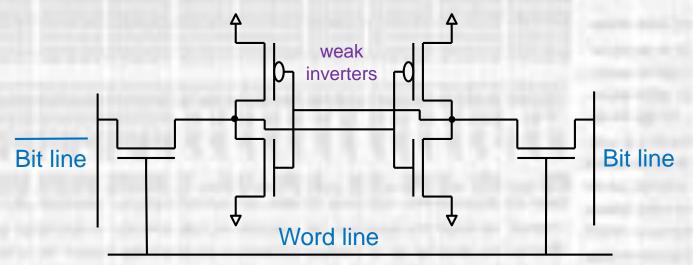
1Gb DDR3 SDRAM 64M x 16



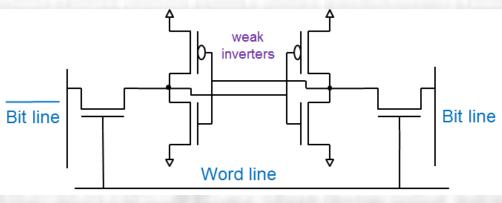
• SRAM

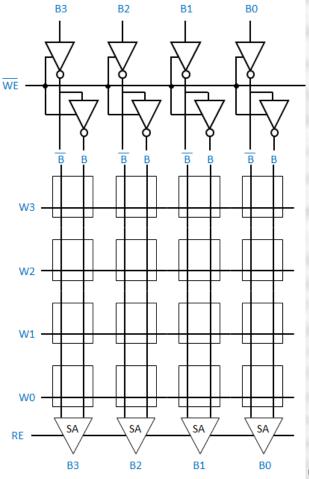
- Latched (feedback) storage elements
 - Requires refresh
- Static
 - As long as power is applied
- Random Access
- Row and Column access architecture
- Synchronous
 - Allows additional bytes to be read/written on a single access

- SRAM Static Random Access Memory
 - Memory cell (1 bit) is based on a feedback circuit
 - Bit value is retained as long as power is maintained
 - Fastest read/write (R/W)
 - Highest power
 - Lowest density
 - Used in caches and small data memories



- SRAM Static Random Access Memory
 - Write
 - All Word lines low
 - Read Enable (RE) disabled (low)
 - Place B0, B1, B2, B3 on inputs
 - Pull write enable bar (WE) low
 - Strobe the desired word line high
 - Bit lines override the bit cell inverters and store the new value in the cell



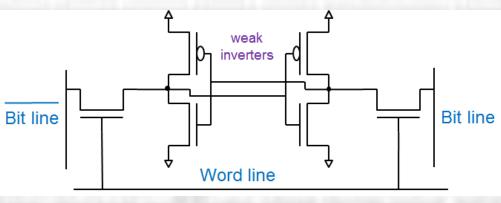


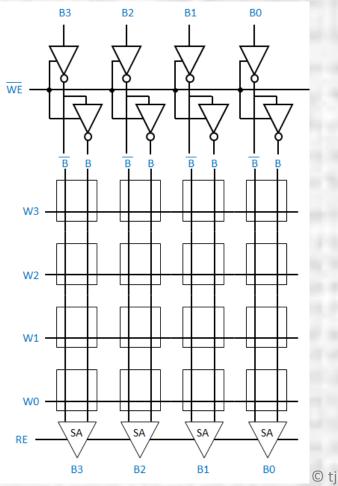
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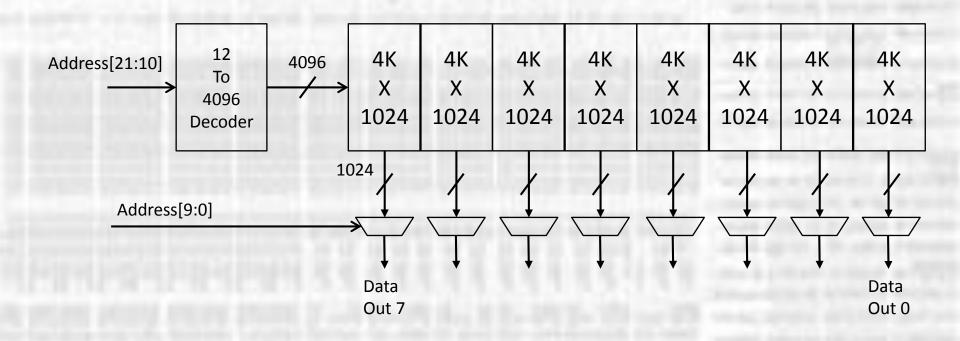
- SRAM Static Random Access Memory
 - Read
 - All Word lines low
 - Write enable bar (WE) high
 - inverters tristated
 - Read Enable (RE) high
 - Strobe the desired word line high
 - Bit cell inverters drive the bit lines and sense amplifiers read the value



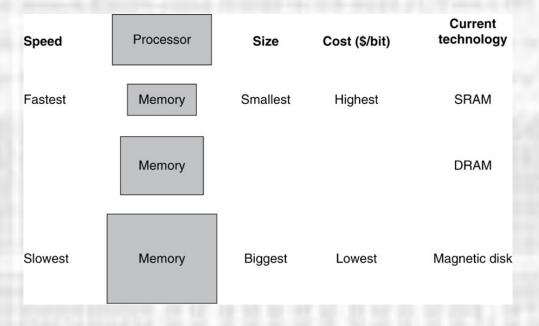




- SRAM
 - Array Layout 4M X 8

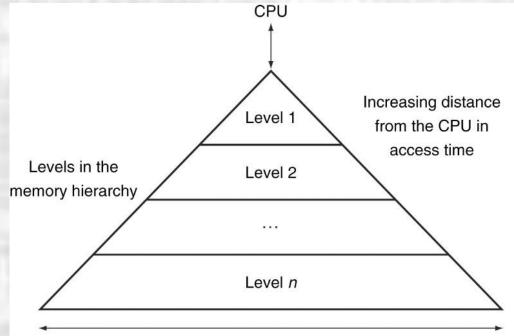


Memory Comparison



Technology	Typ Access Time	\$/Gbyte (2012)
SRAM	0.5 - 2.5 ns	\$500 - \$1000
DRAM	50 - 70 ns	\$10 - \$20
Flash	5,000 - 50,000 ns	\$0.75 - \$2.00
Hard Disk	5,000,000 - 30,000,000 ns	\$0.05 - \$0.10

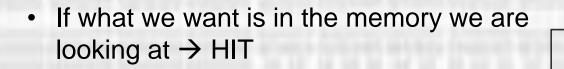
- Critical Memory Considerations
 - Largest slowest
 - Fastest most expensive
 - Can't have everything in a single solution
 - → Memory Hierarchy
 - Issue with a hierarchy
 - Must transfer data up and down the hierarchy
 - As slow as the slowest level addressed



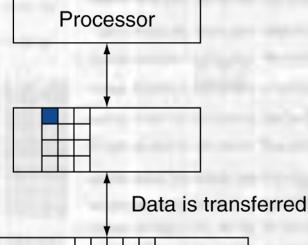
Size of the memory at each level

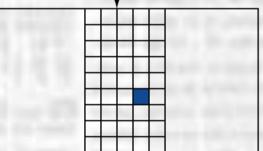
- Memory Hierarchy Considerations
 - Two aspects of processor applications make a memory hierarchy workable
 - Temporal Locality
 - You are more likely to uses something you recently used
 - Loops, calculated values, ...
 - Spatial Locality
 - You are likely to use something that is close to something you recently used
 - Linear code, small loops, data structures

- Memory Hierarchy Considerations
 - Transitions are limited between adjacent levels in the hierarchy
 - Transfer units of information
 - Line or Block
 - Different for each level



If what we want is not in the memory we are looking at → MISS





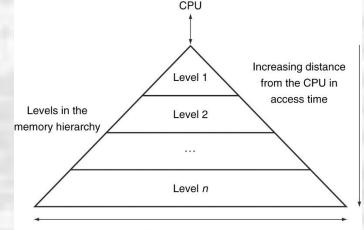
- Memory Hierarchy Considerations
 - Typical System

Registers

Cache (SRAM)

Main Memory (DRAM)

Storage (HDD or Flash)



Size of the memory at each level

- Advanced systems may have 2,3,4 levels of cache
 - Each is progressively slower and larger
 - Size is targeted at holding entire applications